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FACSIMILE TRANSMISSION COVER SHEET

September 3, 2002

To: Angel RomanFrom: Bruce HermanYour Ref.: 09/936,041Our Ref.: 110553Number of Pages Sent (Including cover sheet): 5Prepared By: BAH**Comments:**

Further to our personal interview of August 20, 2002, we enclose a Supplemental Amendment and Appendix in the above-identified application.

Sent by: BAH

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JHOPATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Ichio YUDASAKA et al.

Group Art Unit: 2812

Application No.: 09/936,041

Examiner: Angel Roman

Filed: December 18, 2001

Docket No.: 110553

For: METHOD FOR MANUFACTURING A THIN-FILM TRANSISTOR COMPRISING A RECOMBINATION CENTER (AS AMENDED)

SUPPLEMENTAL AMENDMENT UNDER 37 C.F.R. §1.111Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

As a supplement to the Amendment filed on August 2, 2002, and further to a personal interview with Examiner Roman conducted on August 20, 2002, please further amend the above the above-identified application as follows:

IN THE CLAIMS:

Please replace claim 14 as follows:

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14. (Amended) A method of manufacturing a display device comprising a thin-film transistor that is manufactured by:
- forming a channel region facing a gate electrode through a gate insulating film;
 - forming source and drain regions connected to the channel region in a semiconductor film that is formed on a surface of an insulating substrate; and
 - forming a recombination center that captures carriers in the channel region by introducing an impurity into said channel region so that a distance between the recombination